

1.Base 2.Collector 3.Emitter

NPN Triple Diffused Planar Silicon Transistor

Absolute Maximum Ratings $T_{C}=25^{\circ}C$ unless otherwise noted Symbol Parameter Rating Units V_{CBO} Collector-Base Voltage 1500 V ٧ V_{CEO} Collector-Emitter Voltage 750 V V_{EBO} Emitter-Base Voltage 6 Collector Current (DC) 10 А I_{C} Collector Current (Pulse) 20 А I_{CP}* P_C **Collector Dissipation** 60 W 150 °C T_J Junction Temperature T_{STG} Storage Temperature -55 ~ 150 °C

* Pulse Test: Pulse Width=5ms, Duty Cycle < 10%

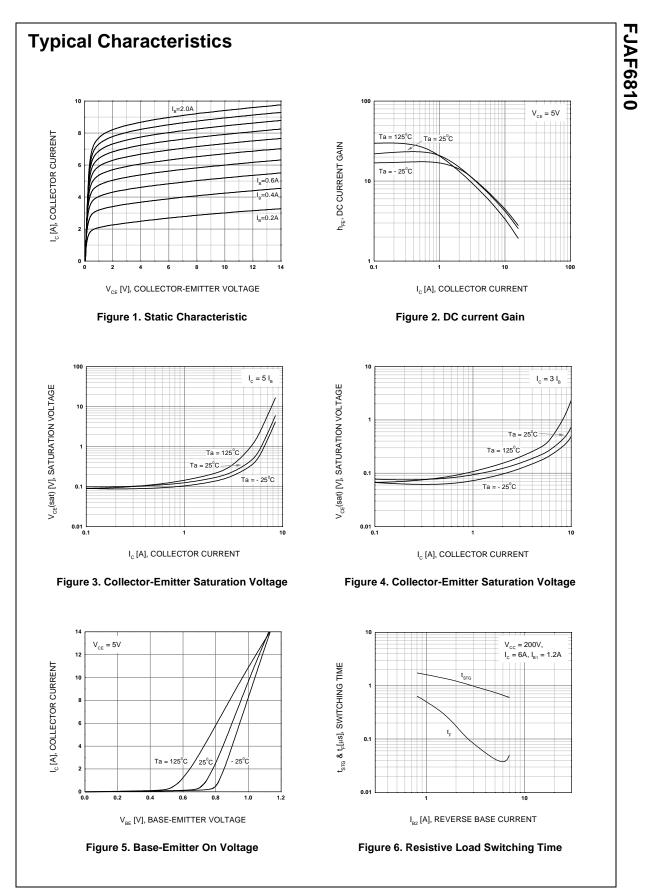
Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	I Parameter Test Conditions		Min	Тур	Max	Units
I _{CES}	Collector Cut-off Current	V _{CB} =1400V, R _{BE} =0			1	mA
I _{CBO}	Collector Cut-off Current	V _{CB} =800V, I _E =0			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB}=4V, I_{C}=0$			1	mA
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =500μA, I _C =0	6			V
h _{FE1} h _{FE2}	DC Current Gain	V _{CE} =5V, I _C =1A V _{CE} =5V, I _C =6A	10 5		8	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =6A, I _B =1.5A			3	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C =6A, I _B =1.5A			1.5	V
t _{STG} *	Storage Time	V_{CC} =200V, I_{C} =6A, R_{L} =33 Ω			3	μs
t _F *	Fall Time	I _{B1} =1.2A, I _{B2} = - 2.4A			0.2	μs

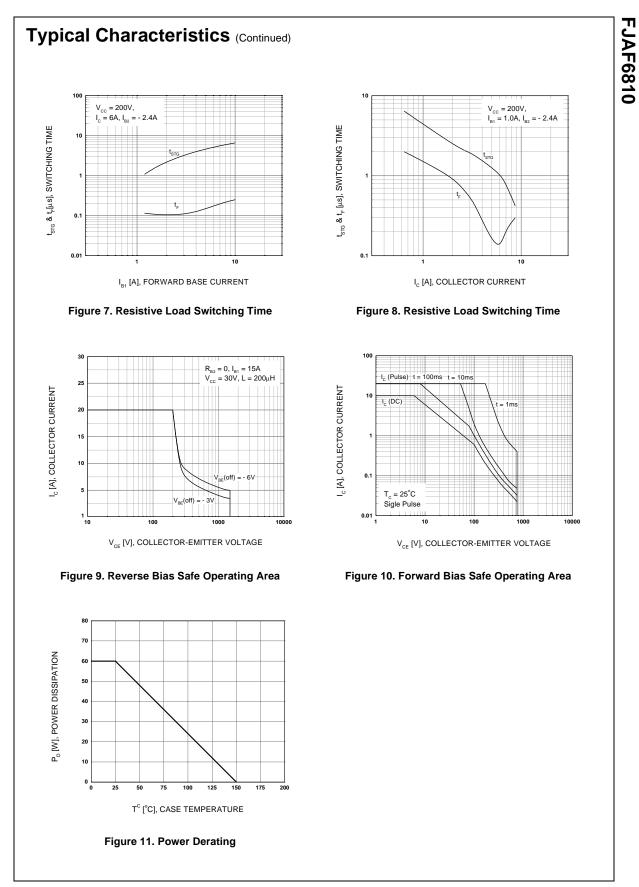
* Pulse Test: PW=20 μ s, duty Cycle=1% Pulsed

Thermal Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Тур	Max	Units
R _{θjC}	Thermal Resistance, Junction to Case		2.08	°C/W

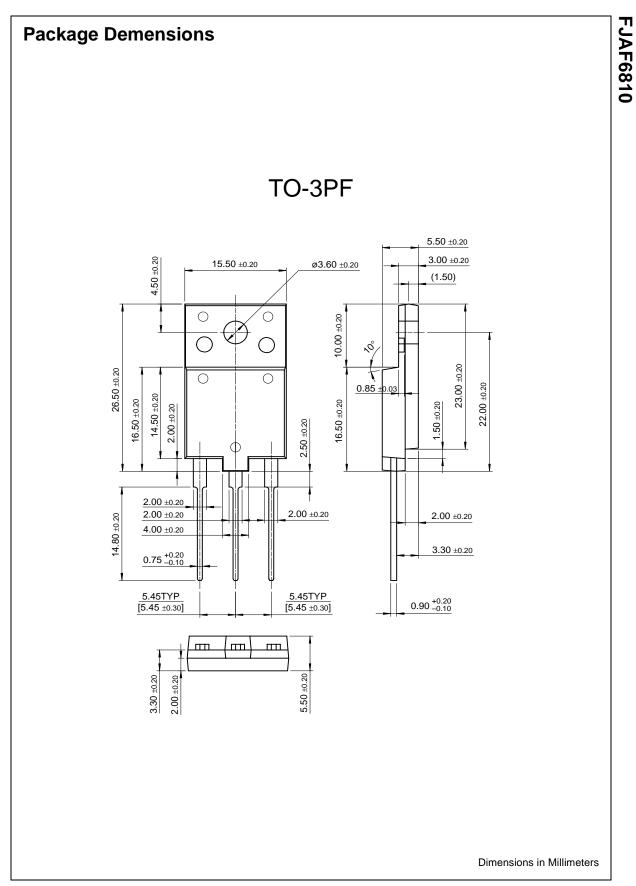


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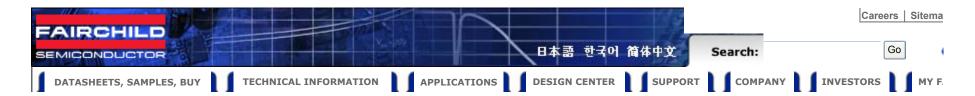
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Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.



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FJAF6810

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Features

High Voltage Color Display Horizontal Deflection Output

- High Collector-Base Breakdown Voltage : BV_{CBO} = 1500V
- High Switching Speed : t_F (typ.) =0.1.µs
- For Color Monitor

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Product status/pricing/packaging

001
Datasheet
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EDF

BUV



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Product	Product status	Pb-free Status	Package type	Leads	Packing method	Package Marking Convention**
FJAF6810ATU	Lifetime Buy	Ø	TO-3PF	3	RAIL	N/A
FJAF6810AYDTBTU	Lifetime Buy	Ø	TO-3PF	3	RAIL	Line 1: \$Y (Fairchild logo)
FJAF6810TU	Lifetime Buy	Ø	TO-3PF	3		Line 1: \$Y (Fairchild logo) Line 2: J6810 Line 3: &3

Indicates product with Pb-free second-level interconnect. For more information <u>click here.</u>

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